# Complementary Bias Resistor Transistors R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ NPN and PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

(T<sub>A</sub> = 25°C both polarities Q<sub>1</sub> (PNP) & Q<sub>2</sub> (NPN), unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	Ic	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MUN5336DW1T1G	SOT-363	3,000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

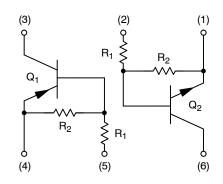
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#### **PIN CONNECTIONS**



#### MARKING DIAGRAM



SOT-363 CASE 419B



36 = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

<sup>\*</sup>Date Code orientation may vary depending upon manufacturing location.

# THERMAL CHARACTERISTICS

Characteristic			Max	Unit
MUN5336DW1 (SOT-363) ONE JUNCTION HEATED				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	187 256 1.5 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	670 490	°C/W
MUN5336DW1 (SOT-363) BOTH JUNCTION HEATED (Note 3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	250 385 2.0 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	493 325	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	188 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>sta</sub>	-55 to +150	°C

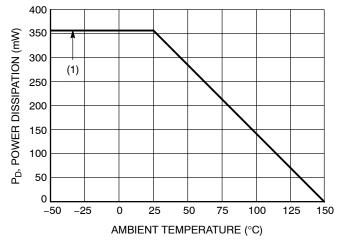
FR-4 @ Minimum Pad.
 FR-4 @ 1.0 × 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C both polarities Q<sub>1</sub> (PNP) & Q<sub>2</sub> (NPN), unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	-	-	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	I <sub>EBO</sub> – -		0.05	mAdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	_	-	Vdc
ON CHARACTERISTICS	<u> </u>				
DC Current Gain (Note 4) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	150	_	
Collector-Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	V <sub>CE(sat)</sub>	-	-	0.25	V
Input Voltage (Off) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 $\mu$ A) (NPN) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 $\mu$ A) (PNP)	V <sub>i(off)</sub>	- -	1.2 1.2	0.5 0.5	Vdc
Input Voltage (On) $(V_{CE} = 0.3 \text{ V, I}_{C} = 3.0 \text{ mA}) \text{ (NPN)} $ $(V_{CE} = 0.3 \text{ V, I}_{C} = 3.0 \text{ mA}) \text{ (PNP)}$	V <sub>i(on)</sub>	3.0 3.0	1.7 1.6	- -	Vdc
Output Voltage (On) ( $V_{CC} = 5.0 \text{ V}, V_B = 5.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (Off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.



(1) SOT-363;  $1.0 \times 1.0$  Inch Pad

Figure 1. Derating Curve

# TYPICAL CHARACTERISTICS MUN5336DW1 - NPN

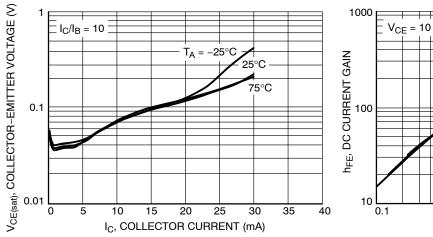


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

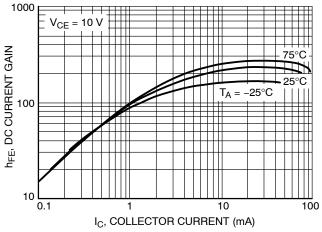


Figure 3. DC Current Gain

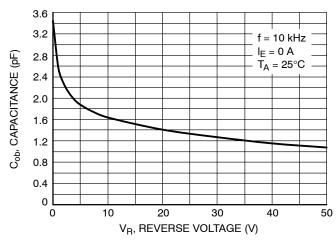


Figure 4. Output Capacitance

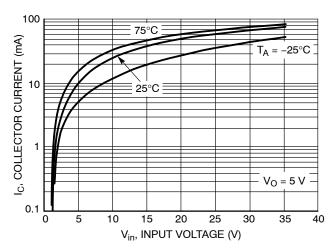


Figure 5. Output Current vs. Input Voltage

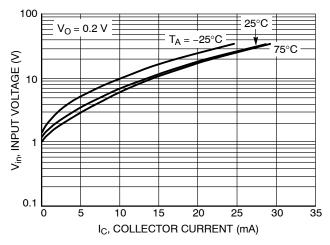


Figure 6. Input Voltage vs. Output Current

# TYPICAL CHARACTERISTICS MUN5336DW1 - PNP

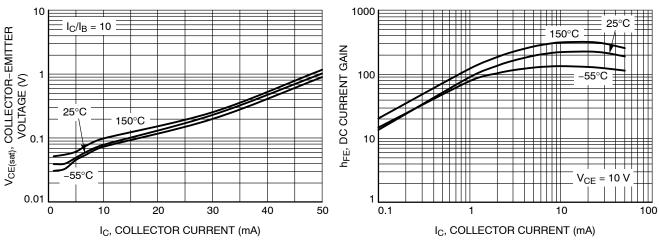


Figure 7. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 8. DC Current Gain

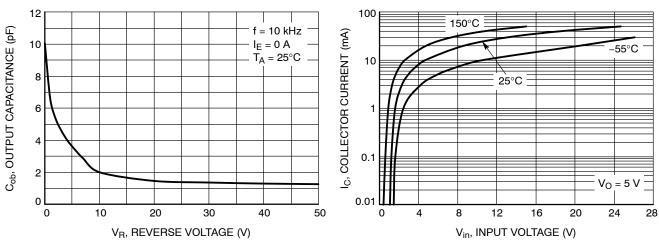


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

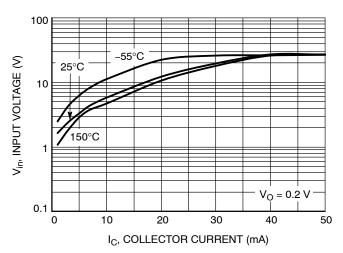
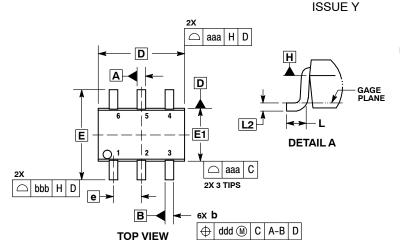
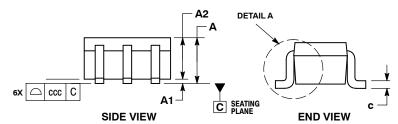


Figure 11. Input Voltage vs. Output Current

#### PACKAGE DIMENSIONS

#### SC-88/SC70-6/SOT-363 CASE 419B-02



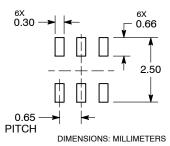


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- DIMENSIONING AND INSERTING PER ASMET 14.5M, 1994
  CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
- DATUMS A AND B ARE DETERMINED AT DATUM H.
  DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE
  LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION.
- ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α		-	1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
E	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е	(	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018	
L2		0.15 BS	C	0.006 BSC			
aaa		0.15			0.006		
bbb	0.30			0.012			
ccc	0.10			0.004			
ddd		0.10		0.004			

#### RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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